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The invention relates to the field of thermo-electric materials, namely to processes for recrystallization of microwires of anisotropic materials in glass insulation. The process for recrystallization of bismuth-based microwire in glass insulation consists in moving the microwire inside a capacitor, formed by two copper plates, generating a strong electric field, heating the microwire with a laser beam to the core melting temperature with the formation of a narrow molten zone, which in the direction of the microwire movement inside the capacitor is immediately crystallized by an air flow, with the direction of the crystallographic axis C_3 of the microwire in the direction of the electric field.

Claims: 1

Fig.: 1